


[Home](#) > [JANS2N5416UA \(#70527\)](#)

JANS2N5416UA (#70527)

Products

- ▶ [Product Directory](#)
- ▶ [Applications Directory](#)
- ▶ [Parametric Search](#)

Overview

Docs & Specs

Description

This family of 2N5415UA and 2N5416UA epitaxial planar transistors are military qualified up to a JANS level for high-reliability applications. The UA package is hermetically sealed and provides a low profile for minimizing board height. These devices are also available in the long-leaded TO-5, short-leaded TO-39 and low profile U4 packaging.

Electrical Rating	Symbol	Min	Typ	Max	Unit
DC Current Gain	HFE	30.00		120.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector Current (dc)	I_C			1.00	A
Collector-Emitter Voltage (Base Open)	V_{CEO}			300.00	V
Junction Temperature (°C)	T_J			200.00	°C

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